What is claimed is:

1. A magnetoresistive element comprising at least a pair of ferromagnetic layers stacked with having an intermediate layer inbetween so as to face each other, wherein said element achieves a change in the magnetic resistance by permitting an electric current to flow in the direction which crosses the plane of the stacked layers,

wherein at least one of said ferromagnetic layers constituting an information recording layer has an amorphous structure comprising either a CoFeB alloy or a CoFeNiB alloy,

wherein said information recording layer has a plane form having a longer axis in one direction wherein both sides of the plane form along the longer axis direction form one of a straight line and an outward protrusion , and the both ends of the plane form in the longer axis direction form a outward protrusion, thereby forming a pattern form,

wherein said pattern form has an aspect ratio in the range of 1:1.2 to 1:3.5, in terms of shorter axis length : longer axis length.

2. The magnetoresistive element according to claim 1, wherein the plane form of said information recording layer has symmetry with respect to the center axis in each of the longer axis direction and the shorter axis direction.

3. The magnetoresistive element according to claim 1, wherein, in the plane form of said information recording layer, both sides of the plane form along the longer axis direction form an elliptic form or an oval form which are curved or bent outward.

4. A magnetic memory unit having a word line and a bit line which spatially cross, and comprising a magnetoresistive element constituting a memory device in a portion at which the word line and the bit line spatially cross,

wherein said magnetoresistive element comprises at least a pair of ferromagnetic layers stacked with having an intermediate layer inbetween so as to face each other, wherein said element achieves a change in the magnetic resistance by permitting an electric current to flow in the direction which crosses the plane of the stacked layers,

wherein at least one of said ferromagnetic layers constituting an information recording layer has an amorphous structure comprising either a CoFeB alloy or a CoFeNiB alloy,

wherein said information recording layer has a plane form having a longer axis in one direction wherein both sides of the plane form along the longer axis direction form one of a straight line and an outward protrusion, and the both ends of the plane form in the longer axis direction form an outward protrusion, thereby forming a pattern form,

wherein said pattern form has an aspect ratio in the range of 1:1.2 to 1:3.5, in terms of shorter axis length: longer axis length.

5. The magnetic memory unit according to claim 4, wherein the plane form of said information recording layer has symmetry with respect to the center axis in each of the longer axis direction and the shorter axis direction.

6. The magnetic memory unit according to claim 4, wherein, in the plane form of said information recording layer, both

sides of the plane form along the longer axis direction form an elliptic form or an oval form which are curved or bent outward.